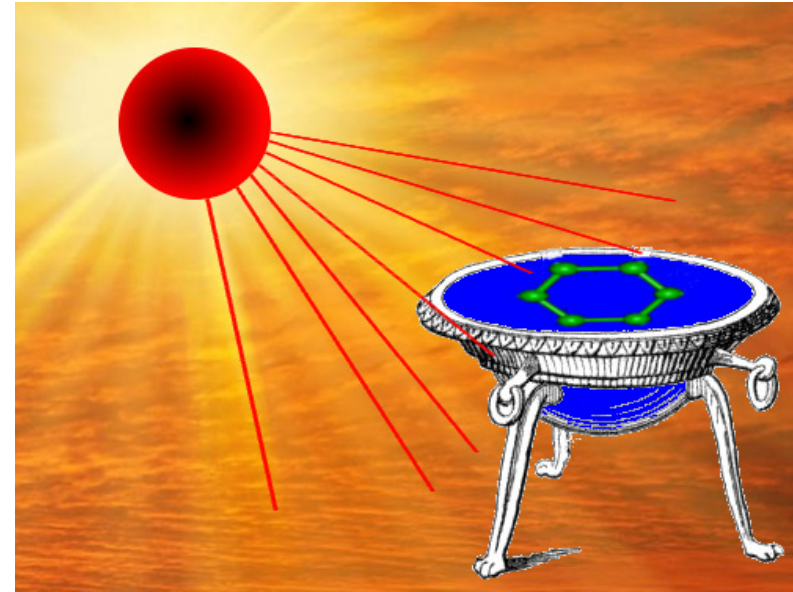


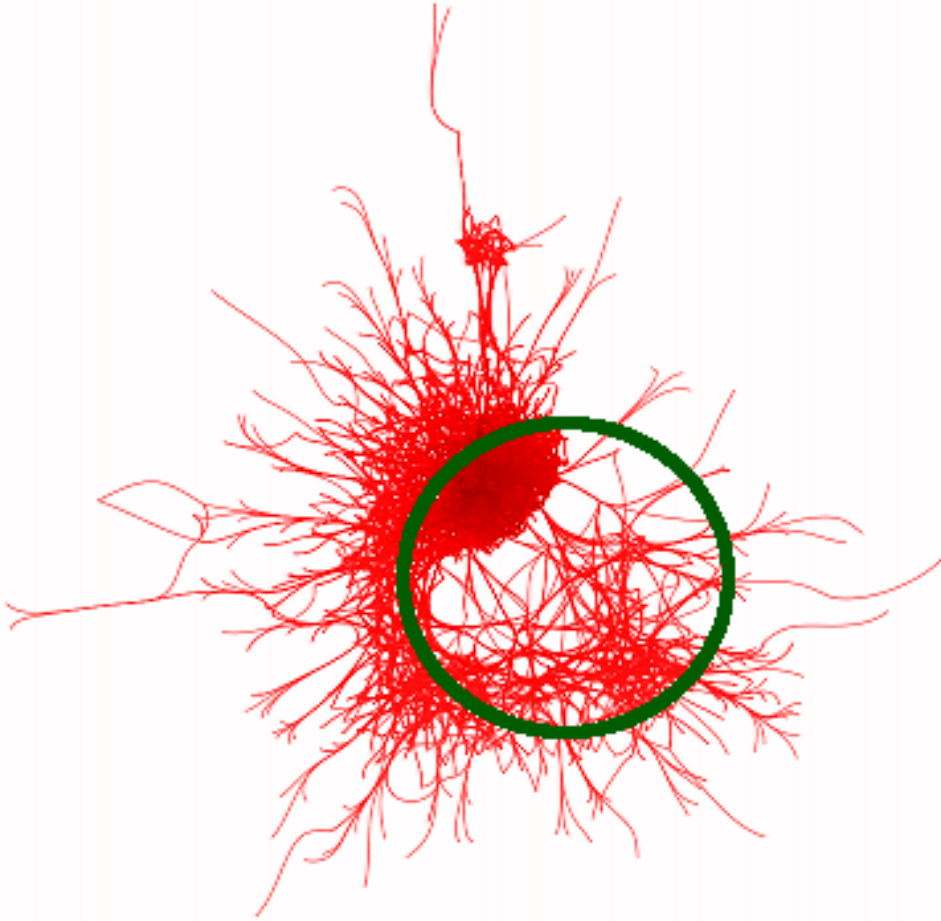
The non-equilibrium steady state and induced current
in mesoscopically glassy systems with non trivial topology:
Interplay of resistor-network theory and Sinai physics

Daniel Hurowitz, Ben-Gurion University

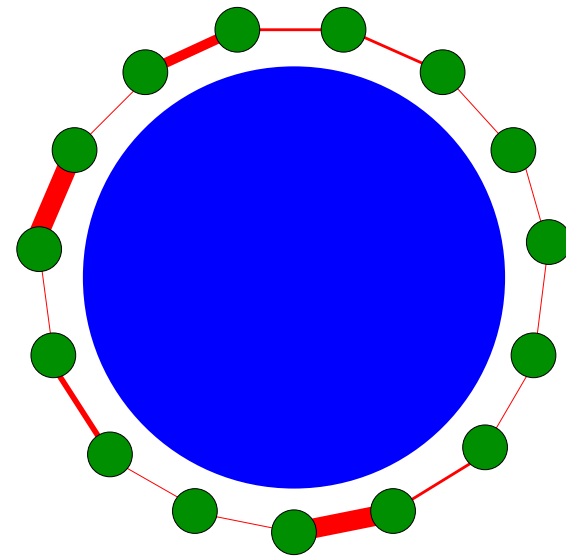


- [1] D. Hurowitz and D. Cohen, Europhysics Letters 93, 60002 (2011)
- [2] D. Hurowitz, S. Rahav and D. Cohen, Europhysics Letters 98, 20002 (2012)
- [3] D. Hurowitz, S. Rahav and D. Cohen, arXiv (2013)

Sparse systems



$$w_{\vec{n}} = w_{\vec{n}}^{\beta} + \nu g_n$$

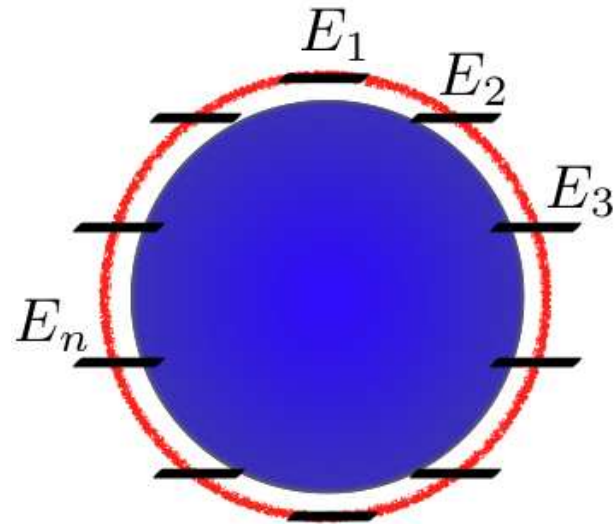


In our study we consider systems that are "sparse" or "glassy", meaning that many time scales are involved.

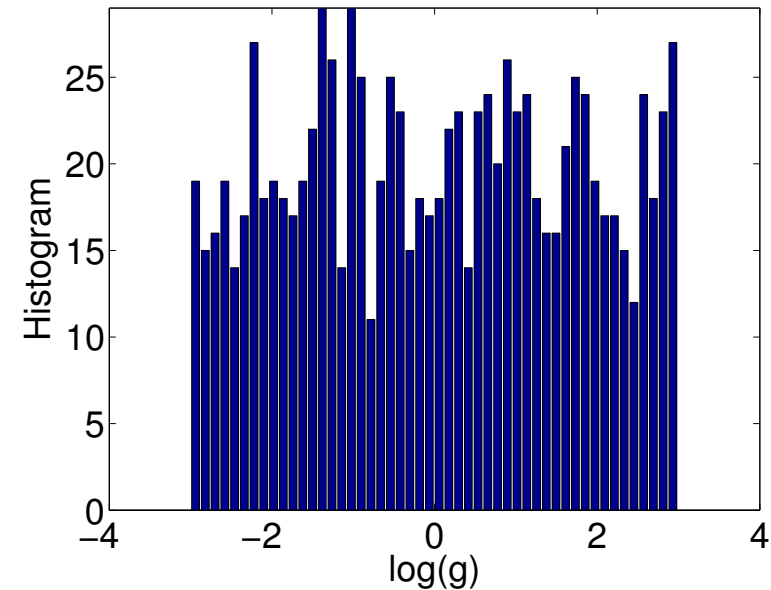
Standard thermodynamics does not apply to such systems.

The model

System + Bath + Driving



Histogram of couplings



$$w_{\vec{n}} = w_{\vec{n}}^{\beta} + \nu g_n$$

$g_n =$ couplings

← $\sigma =$ few decades →

“sparsity” = log wide distribution of couplings

$$w_n^{\nu} = \nu g_n$$

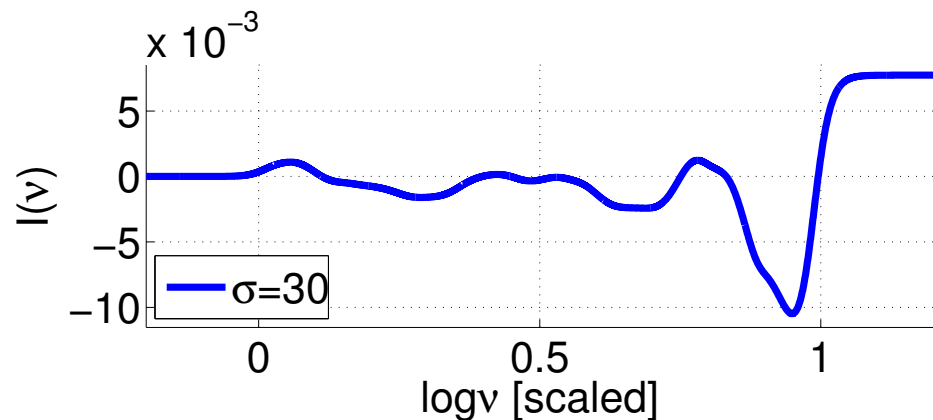
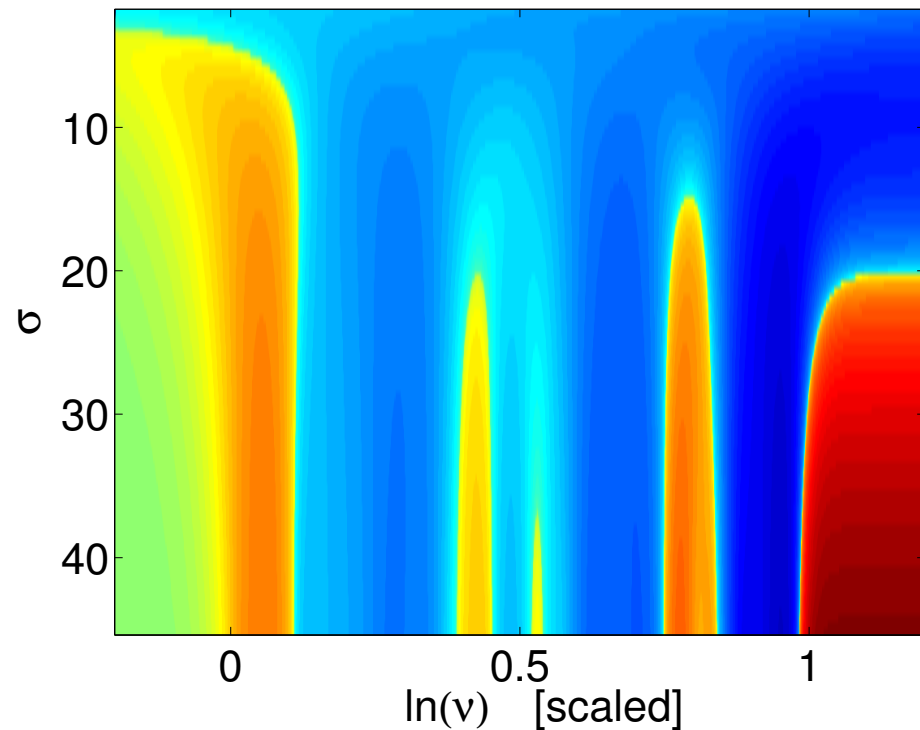
$$\frac{w_{\vec{n}}^{\beta}}{w_{\vec{n}}^{\beta}} = \exp \left[-\frac{E_n - E_{n-1}}{T_B} \right]$$

corresponds to $T_A = \infty$

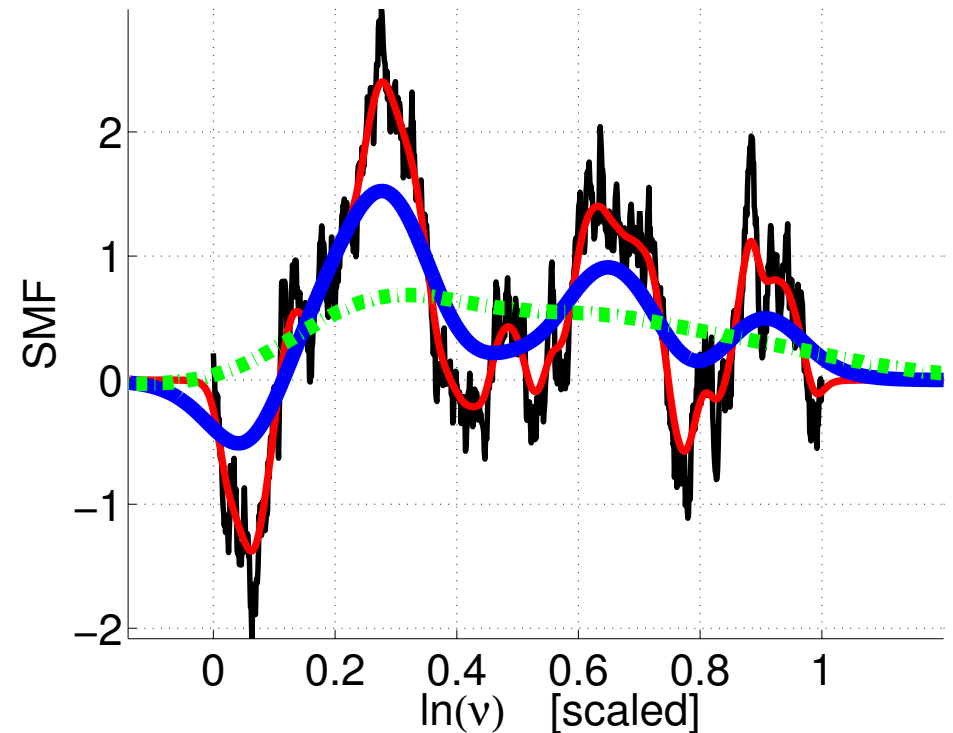
corresponds to $T_B =$ finite

Current sign reversals in the Sinai regime

Current



SMF



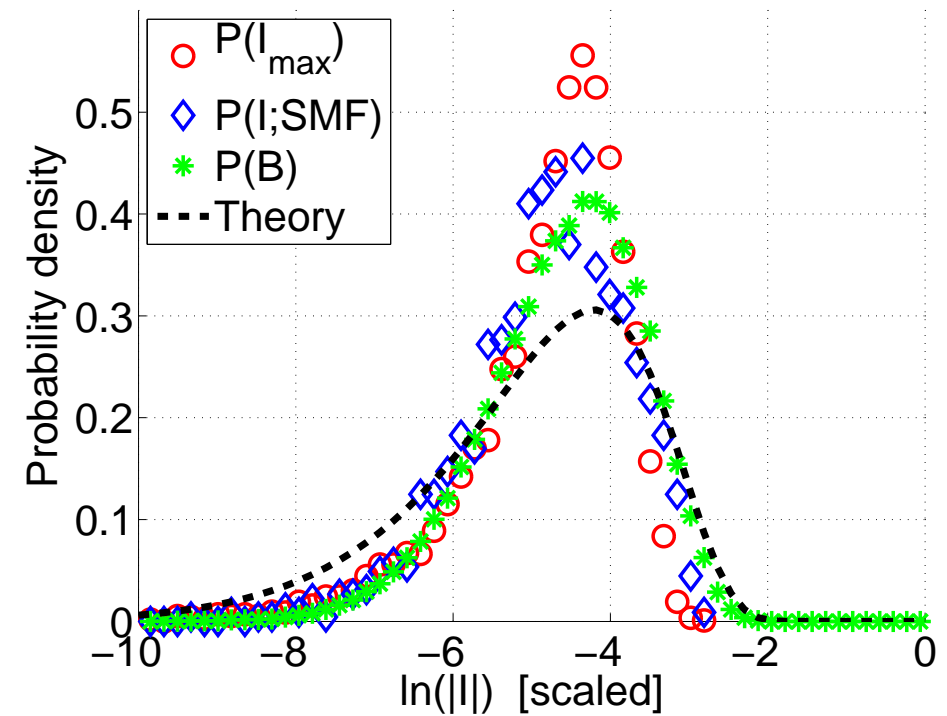
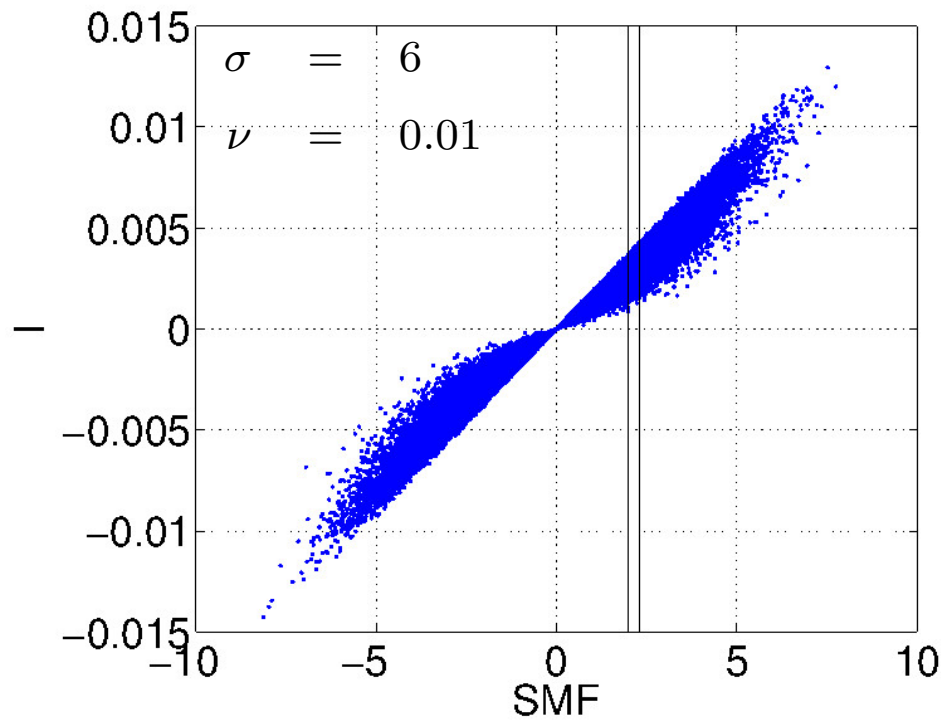
$$I(\nu) \sim \frac{1}{N} w_\varepsilon e^{-B} 2 \sinh\left(\frac{\mathcal{E}_\sigma}{2}\right)$$

\mathcal{E}_σ - Stochastic Motive Force

B - Effective Activation Barrier

The number of sign changes depends on the sparsity $\approx \sqrt{\pi\sigma}$

Statistics of the Current in the Sinai Regime



Single barrier approximation for the current

Barrier distribution

$$I(\nu) \sim \frac{1}{N} w_\varepsilon e^{-B} 2 \sinh\left(\frac{\mathcal{E}_\circ}{2}\right)$$

$$\text{Prob}\{\text{barrier} < B\} \sim \exp\left[-\frac{1}{2} \left(\frac{\pi\sigma_B}{2B}\right)^2\right]$$

\mathcal{E}_\circ - Stochastic Motive Force
 B - Effective Activation Barrier

$$\sigma_B^2 = 2\Delta^2 N \frac{\ln(g_{\max}\nu)}{\sigma}$$

The stochastic potential and SMF

Steady state rate equations:

$$I = w_{\vec{n}} p_n - w_{\leftarrow n} p_{n+1}$$

Stochastic field:

$$\mathcal{E}(x_n) \equiv \ln \left[\frac{w_{\vec{n}}}{w_{\leftarrow n}} \right] \approx - \left[\frac{1}{1 + g_n \nu} \right] \frac{E_n - E_{n-1}}{T_B}$$

Stochastic potential:

$$V(x) = - \int^x \mathcal{E}(x') dx' \approx \sum_n \left[\frac{1}{1 + g_n \nu} \right] \frac{E_n - E_{n-1}}{T_B}$$

Stochastic Motive Force:

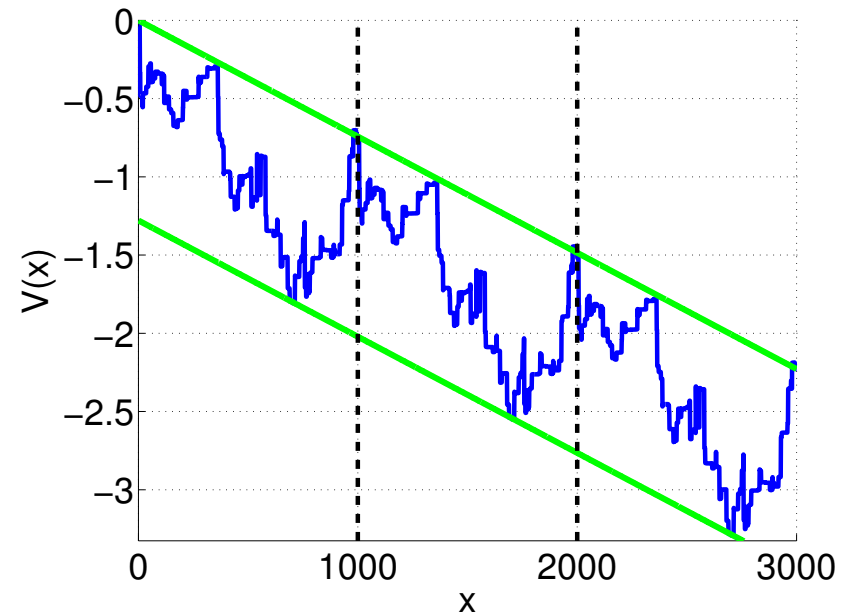
$$\mathcal{E}_{\circlearrowleft} \equiv \ln \left[\frac{\prod_n w_{\vec{n}}}{\prod_n w_{\leftarrow n}} \right] = \oint \mathcal{E}(x) dx \text{ if no driving} = 0$$

Our model:

Telescopic correlations:

$$\mathcal{E}(x_n) \sim \Delta_n \equiv (E_n - E_{n+1})$$

Yet... we have sparsely distributed couplings



Sinai diffusion [1982]:

Random, Uncorrelated & non symmetric transition rates

\rightsquigarrow Buildup of activation barrier $B \sim \sqrt{N}$

\rightsquigarrow Exponentially low current $I \sim e^{-\sqrt{N}}$

SMF vs. Driving intensity

Stochastic Motive Force

$$\mathcal{E}_{\odot}(\nu) \approx - \sum_{n=1}^N \left[\frac{1}{1 + g_n \nu} \right] \frac{E_n - E_{n-1}}{T_B}$$

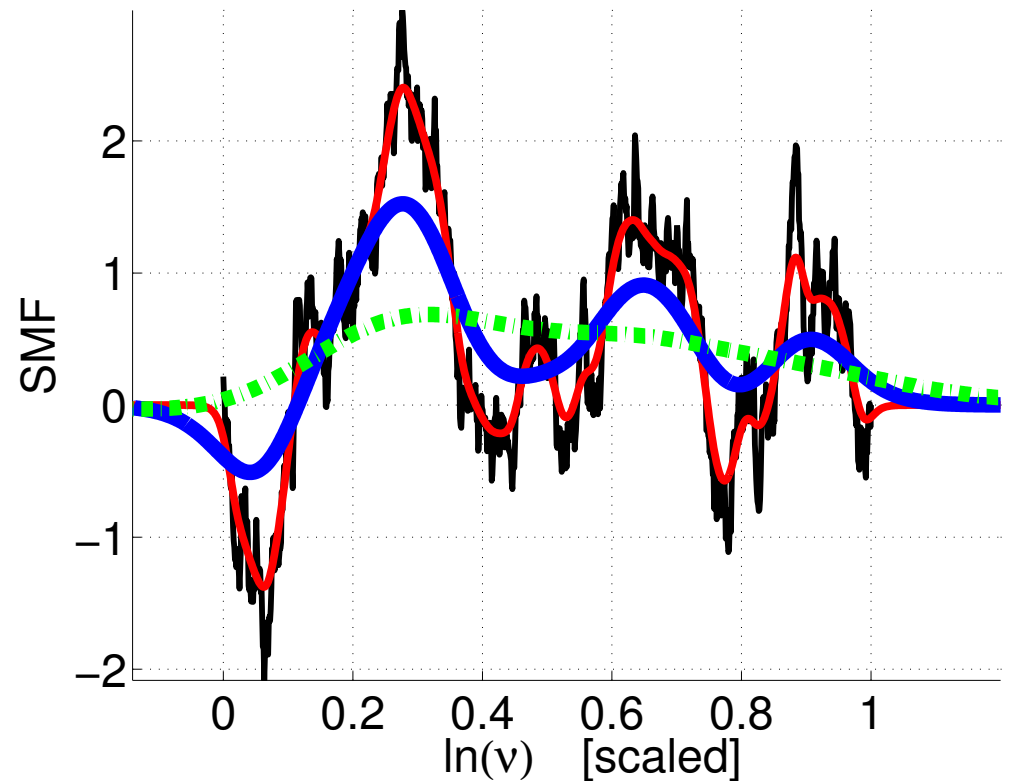
$$\tau \equiv \frac{1}{\sigma} \ln(g_{\max} \nu), \quad \tau_n = \frac{1}{\sigma} \ln \left(\frac{g_{\max}}{g_n} \right)$$

$$\sigma = \ln \frac{g_{\max}}{g_{\min}}, \quad [\text{log-width of distribution}]$$

Coarse grained random walk:

$$\mathcal{E}_{\odot}(\tau) = - \sum_{n=1}^N f_{\sigma}(\tau - \tau_n) \frac{E_n - E_{n-1}}{T_B}$$

$$f_{\sigma}(t) \equiv [1 + e^{\sigma t}]^{-1} \quad [”step” \text{ function}]$$



$$\text{Sinai regime: } \frac{1}{g_{\max}} < \nu < \frac{1}{g_{\min}} \\ 0 < \tau < 1$$

Expected number of sign changes $\approx \sqrt{\pi \sigma}$

Barrier Statistics

Activation Barrier \equiv Occupation range of a random walk.

$$B \approx \frac{1}{2} \left[\max\{U\} - \min\{U\} \right] \equiv 2R$$

- Joint probability that a RW occupies the interval $[x_a, x_b]$:

$$P_t(x_a, x_b) \equiv \text{Prob}(x_a < x(t') < x_b), \quad t' \in [0, t]$$

$$f(x_a, x_b) = -\frac{d}{dx_a} \frac{d}{dx_b} P_t(x_a, x_b)$$

- Make the transformation $X = \frac{x_a + x_b}{2}$, $R = x_b - x_a$

- A random walk process occupies range R :

$$f(R) = \partial_R^2 \left[R P_t(R) \right]$$

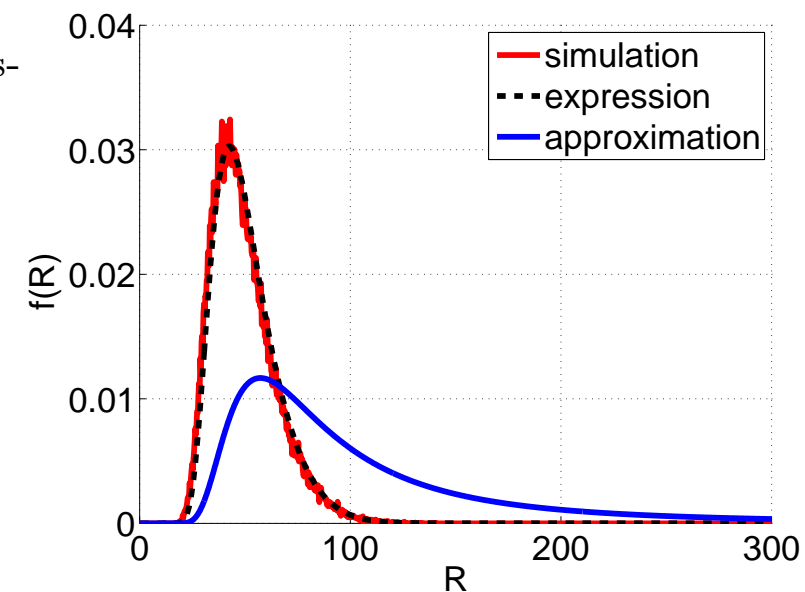
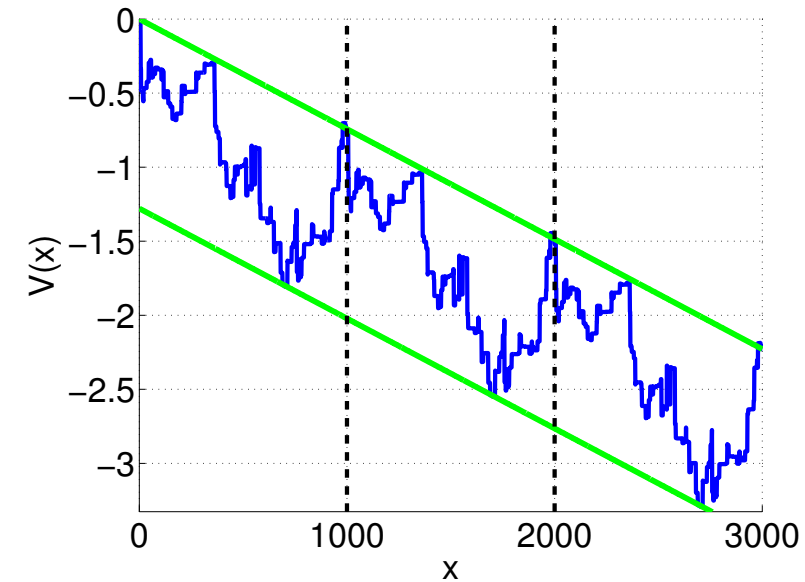
Survival probability of a diffusion process with initial uniform distribution: $P_t(R)$

- Solution to diffusion equation

$$\rho_t(x) = \sum_{n=1,3,5,\dots}^{\infty} \exp \left[-D \left(\frac{\pi n}{R} \right)^2 t \right] \frac{4}{\pi n R} \sin \left(\frac{\pi n}{R} x \right)$$

$$P_t(R) = \int_0^R \rho_t(x) dx = \sum_{n=1,3,5,\dots}^{\infty} \frac{8}{\pi^2 n^2} \exp \left[-D \left(\frac{\pi n}{R} \right)^2 t \right]$$

$$P_t(r) \approx \exp \left(-\frac{1}{2} \left(\frac{\pi \sigma}{R} \right)^2 \right)$$



Summary of main results

1. Number of current sign changes is determined by **log-width** of coupling distribution,

Expected number of sign changes $\approx \sqrt{\pi\sigma}$.

2. The current in the **Sinai** regime may be estimate by a **single barrier approximation**,

$$I(\nu) \sim \frac{1}{N} w_\varepsilon e^{-B} 2 \sinh\left(\frac{\varepsilon\mathcal{O}}{2}\right).$$

3. Exact expression for (non-canonical!) NESS occupation probability

$$p_n \propto \left(\frac{1}{w(x_n)}\right)_\varepsilon e^{-(U(n)-U_\varepsilon(n))}$$

reflects **crossover from Sinai spreading to resistor network picture**.

4. Distribution of currents reflects underlying **Barrier**,

random walk occupation range statistics,

$$\text{Prob}\{\text{barrier} < B\} \sim \exp\left[-\frac{1}{2}\left(\frac{\pi\sigma_B}{2B}\right)^2\right], \text{ with } \sigma_B^2 = 2\Delta^2 N \frac{\ln(g_{\max}\nu)}{\sigma}.$$